Title (en)

Light emitting device

Title (de)

Lichtemittierende Vorrichtung

Title (fr)

Dispositif électroluminescent

Publication

EP 2439795 A2 20120411 (EN)

Application

EP 11184572 A 20111011

Priority

KR 20100098923 A 20101011

Abstract (en)

Disclosed is a light emitting structure comprising a first semiconductor layer (122), a second semiconductor layer (126), and an active layer (124) disposed on between the first and second semiconductor layers, a first electrode (130) electrically connected to the first semiconductor layer (122) and a second electrode (150) electrically connected to the second semiconductor layer (126). The first semiconductor layer is formed, at an edge portion thereof, with a hole, in which a portion (134) of the first electrode (130) is arranged.

IPC 8 full level

H01L 33/38 (2010.01); H01L 33/00 (2010.01); H01L 33/20 (2010.01)

CPC (source: EP KR US)

H01L 33/0093 (2020.05 - KR); **H01L 33/20** (2013.01 - KR); **H01L 33/382** (2013.01 - EP KR US); **H01L 33/385** (2013.01 - KR); H01L 33/0093 (2020.05 - EP US); H01L 33/20 (2013.01 - EP US); H01L 33/385 (2013.01 - EP US); H01L 2924/0002 (2013.01 - EP KR US); H01L 2933/0016 (2013.01 - EP KR US)

Citation (applicant)

KR 20100098923 A 20100910 - CHOI EUN SEONG [KR], et al

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

BA ME

DOCDB simple family (publication)

US 2012049229 A1 20120301; **US 8969892 B2 20150303**; CN 102447032 A 20120509; EP 2439795 A2 20120411; EP 2439795 A3 20141112; EP 2439795 B1 20190320; KR 101690508 B1 20161228; KR 20120037266 A 20120419

DOCDB simple family (application)

US 201113270857 A 20111011; CN 201110315352 A 20111011; EP 11184572 A 20111011; KR 20100098923 A 20101011